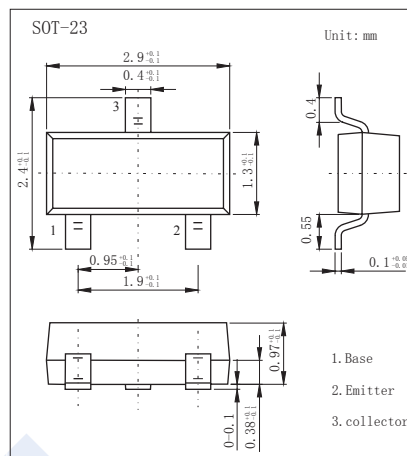


PNP Transistors

KST9015

■ Features

- Complementary to KST9014

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	-50	V
Collector-Emitter Voltage	V_{CEO}	-45	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current -Continuous	I_C	-0.1	A
Collector Power Dissipation	P_C	0.2	W
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to 150	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V_{CBO}	$I_C = -100\mu\text{A}$, $I_E = 0$	-50			V
Collector-emitter breakdown voltage	V_{CEO}	$I_C = -1\text{mA}$, $I_B = 0$	-45			V
Emitter-base Breakdown voltage	V_{EBO}	$I_E = -100\mu\text{A}$, $I_C = 0$	-5			V
Collector cutoff current	I_{CBO}	$V_{CB} = -50\text{V}$, $I_E = 0$			-0.1	μA
Emitter cutoff current	I_{EBO}	$V_{EB} = -5\text{V}$, $I_C = 0$			-0.1	μA
DC current gain	h_{FE}	$V_{CE} = -5\text{V}$, $I_C = -1\text{mA}$	200		1000	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -100\text{mA}$, $I_B = -10\text{mA}$			-0.3	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = -100\text{mA}$, $I_B = -10\text{mA}$			-1	V
Transition frequency	f_T	$V_{CE} = -5\text{V}$, $I_C = -10\text{mA}$, $f = 30\text{MHz}$	150			MHz

■ h_{FE} Classification

Type	KST9015-L	KST9015-H
Range	200-450	450-1000
Marking	M6	

KST9015

■ Typical Characteristics

